9 5 : .> / / x 4 ?ú 3 « | • ’ož
N- CHANNEL MOSFET in a SOT-23 Plastic Package.

8*9 54 - * Š 4 k 9 5 : / x k —)í D }ož
Low $R_{DS(ON)}$,SOT-23 package,HF Product.

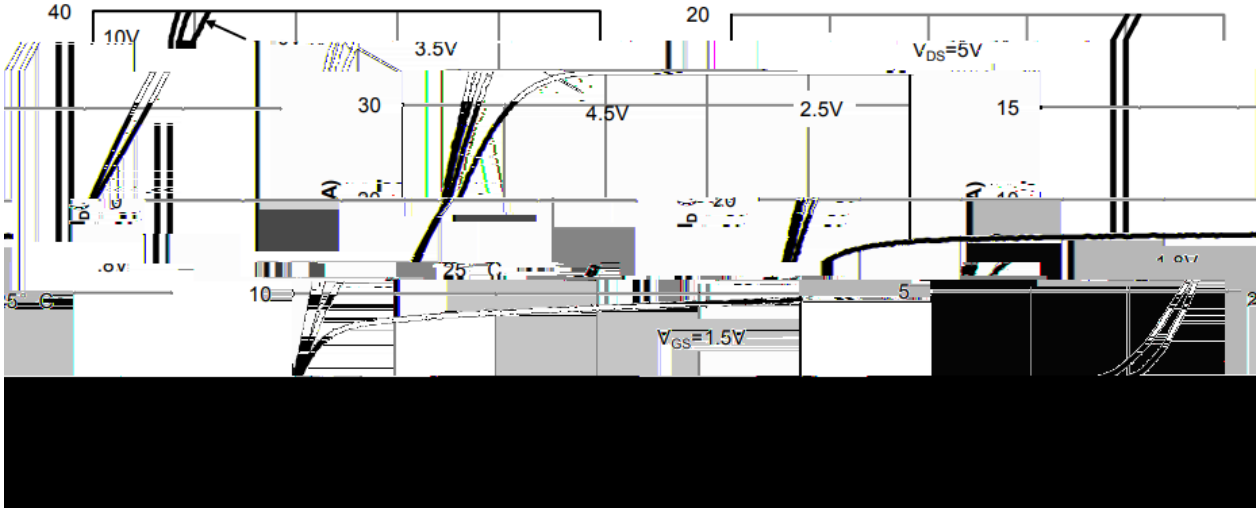
P ’ ò k ä , • ¼ k z ä *) *) ô Eož
Battery management,High speed switch,l

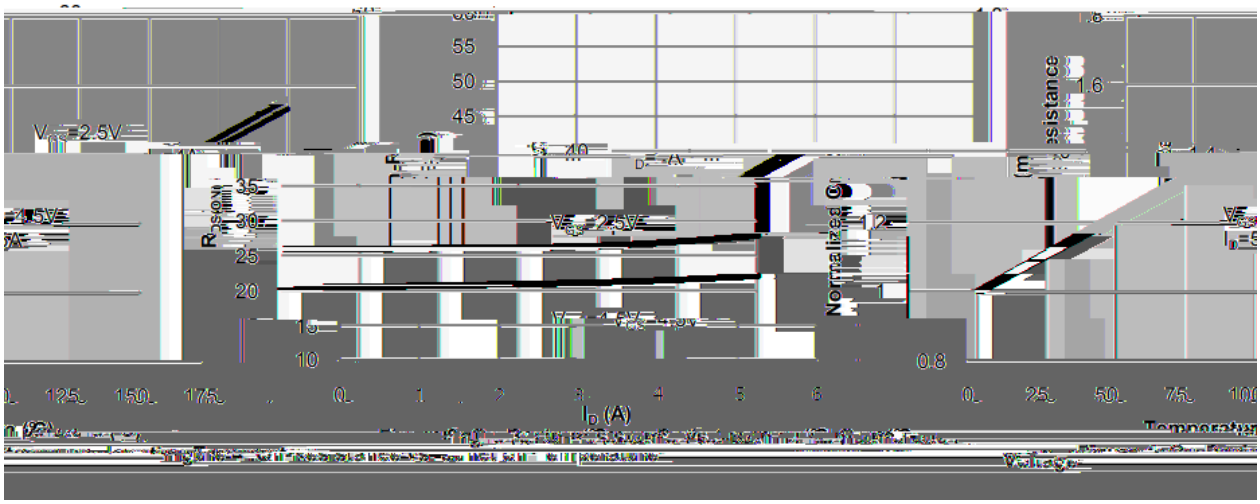
@ *f* Parameter	… Z Symbol	*f* › Rating	% y Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±10	V
Drain Current – Continuous	I_D	4.5	A
Pulsed Drain Current	I_{DM}	12	A
Power Dissipation	P_D	1.4	W
Storage Temperature Range	T_{stg}	-55 150	
Maximum Junction-to-Ambient t 0 10s	R		

Ô4ì × ? d / Electrical Characteristics(Ta=25 ;)

@ *f* Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Total Gate Charge	Q_g(10V)	V_{DS}=10V V_{GS}=10V I_D=4.5A		12.5		nC
Total Gate Charge	Q_g(4.5V)			6		
Gate Source Charge	Q_{gs}			1		
Gate Drain Charge	Q_{gd}			2		
Turn–On Delay Time	$t_{d(on)}$	V_{DS}=10V V_{GS}=10V R_{GEN}=3 R_L=1.7		3		ns
Turn–On Rise Time	t_r			7.5		
Turn–Off Delay Time	$t_{d(off)}$			20		
Turn–Off Fall Time	t_f			6		

Ô ? d • Ž ¢ / Electrical Characteristic Curve





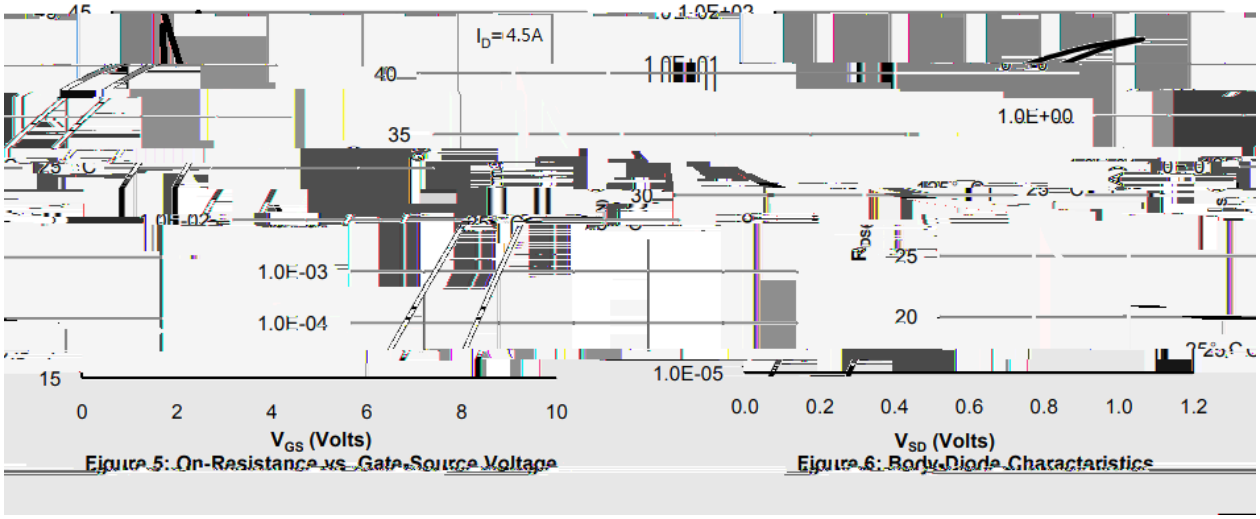
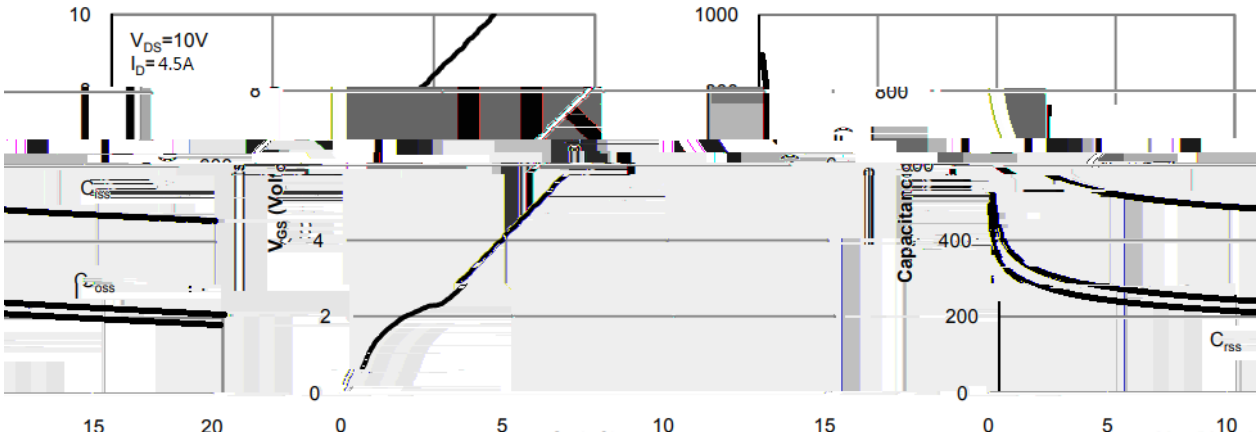


Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

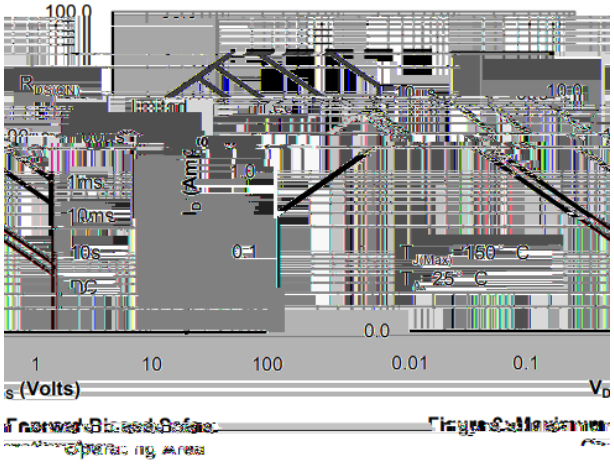
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Characteristics

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance



Operating Area

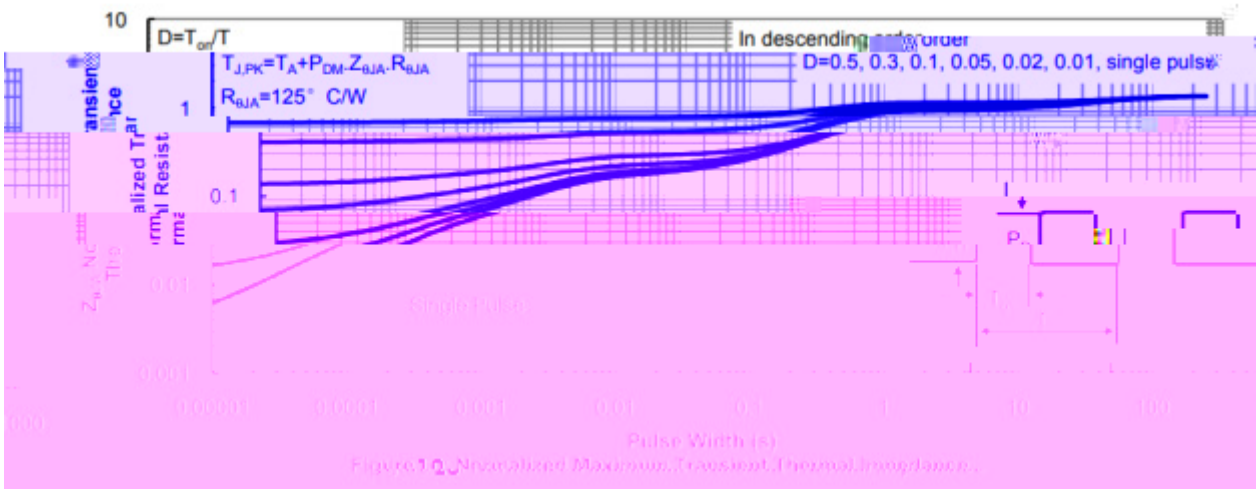
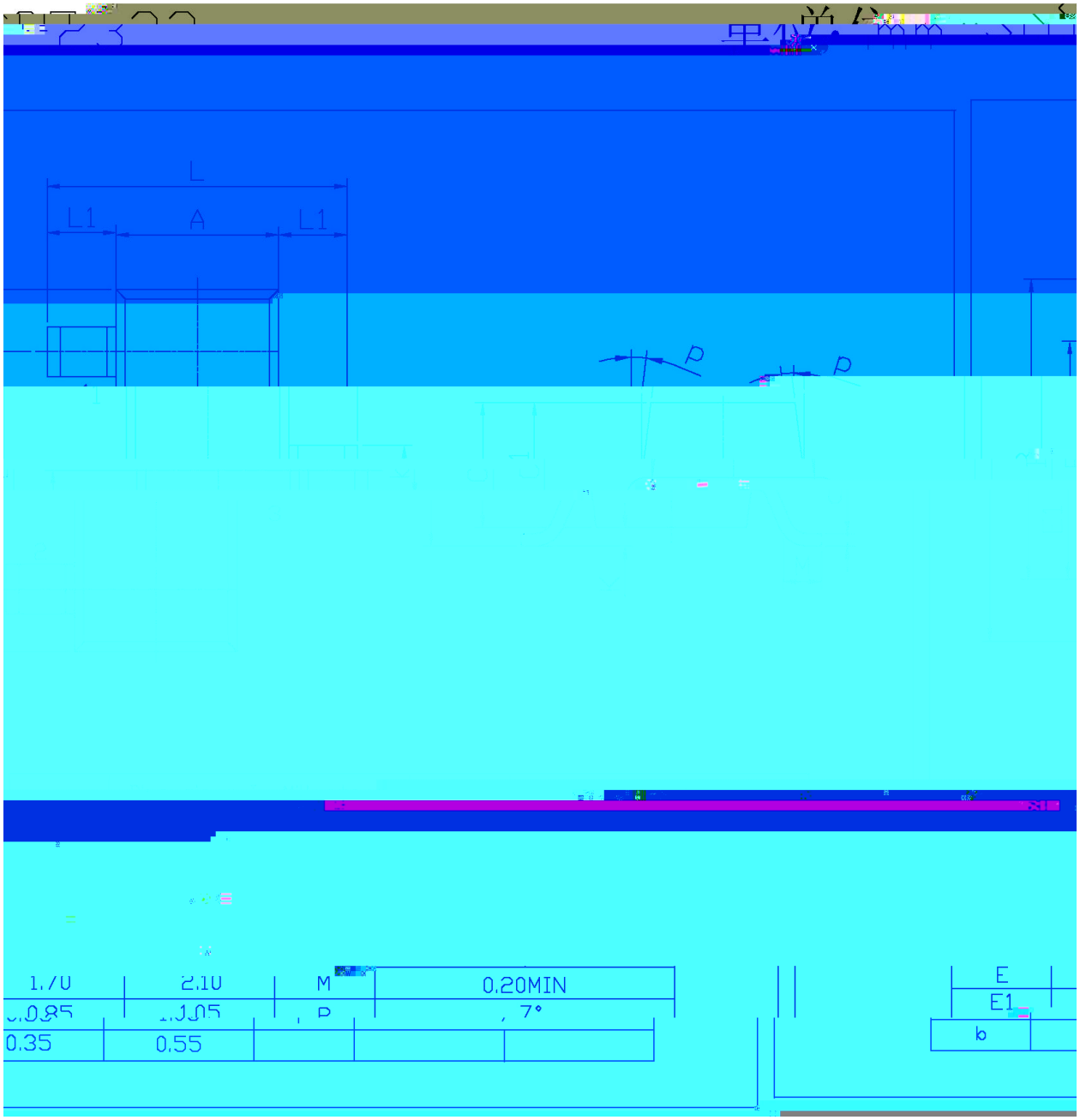
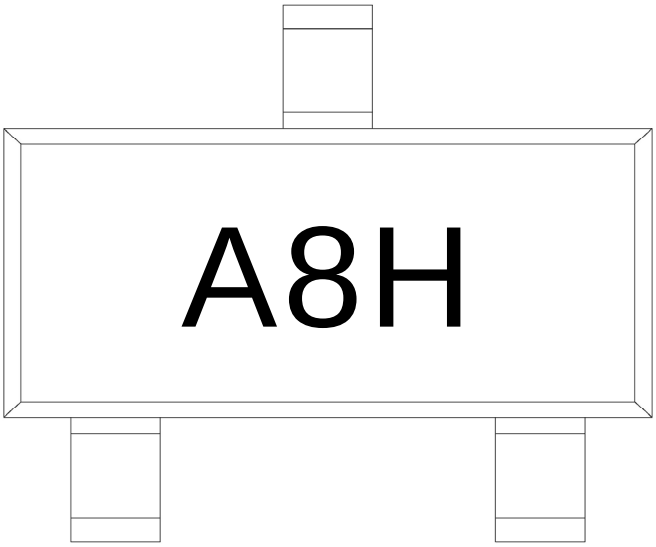


Figure 10 Normalized Maximum Transient Thermal Impedance

Ø ¤ =) ¢ / Package Dimensions



, M y ƒ / Marking Instructions



ª ¢ y

A8: º Z W A

H: ¸ [W A

Note:

A8 y Product Type Code

H: Company Code